

Synthesis and reactions of [tris(trimethylsilyl)methyl]ethyl dichlorosilane

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Abstract

The crowded dichlorosilane TsiSiEtCl₂, (1), (Tsi = (Me₃Si)₃C) was prepared from the reaction between EtSiCl₃ and TsiLi, then it was reduced with LiAlH₄ to give TsiSiEtH₂, (2). The hydride (2) was then treated with two equivalents of ICl/CCl₄ or Br₂/CCl₄ to produce TsiSiEtI₂, (3), and TsiSiEtBr₂, (4), respectively. The reaction of compound (2) with one equivalent of ICl/CCl₄ gives TsiSiEtHI, (5). This product reacted with H₂O/dioxane in the presence of AgClO₄ or with dry MeOH to produce TsiSiEtHOH, (6), and TsiSiEtHOMe, (7), respectively. The compound (3) reacted with H₂O in DMSO/CH₃CN to give TsiSiEt(OH)₂, (8), and the compound TsiSiEtIOMe, (9), was prepared from the reaction of the compound (7) with ICl/CCl₄. When the dichloride (1) was treated with NaOMe/MeOH it gave (Me₃Si)₂CHSiEt(OMe)₂. It is suggested that the reaction proceeds through an elimination–addition mechanism. The dichloride (1) was also treated with KSCN, NaN₃ or NaOCN in CH₃CN to give S_N2 substitution products. All the new products were characterized by FTIR, ¹H NMR, and ¹³C NMR spectroscopy, mass spectrometry and elemental analysis.

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1. Introduction

Much novel chemistry has emerged from studies of the reactions of highly sterically hindered organosilicon compounds of the type TsiSiRX₂ (R = Me, Ph, Bu and X = Cl, Br, I) where Tsi denotes the bulky ligand (Me₃Si)₃C [1–9]. Since the derivatives of TsiSiEtCl₂ had not been synthesized, we thought it would be worthwhile to make them in order to study the reactivity of this crowded dichloride. It has been shown that when the steric hindrance at the functional silicon centers is reduced or linear nucleophiles like N₃[−], SCN[−] and OCN[−] are used, direct bimolecular displacement takes place [10]. Studies have already revealed that nucleophilic attack by alkox-

ide at a silicon center bearing the (Me₃Si)₃C group is inhibited because of the steric hindrance; instead they react with one of the less hindered Me₃Si groups to yield fragmentation products by a mechanism involving sila-olefin (silene) intermediates [11].

2. Results and discussion

Tris(trimethylsilyl)methyl silicon compounds of the type TsiSiRX₂ have been shown to possess unusual properties, which can be attributed to the very large steric hindrance to nucleophilic attack at the silicon atom of the Si–X bond. The observation of unusual mechanisms of reaction at silicon centers in trisyl-silicon compounds is made possible mainly by the marked steric inhibition of direct bimolecular attack. However, with suitable nucleophiles such substitutions do take place.

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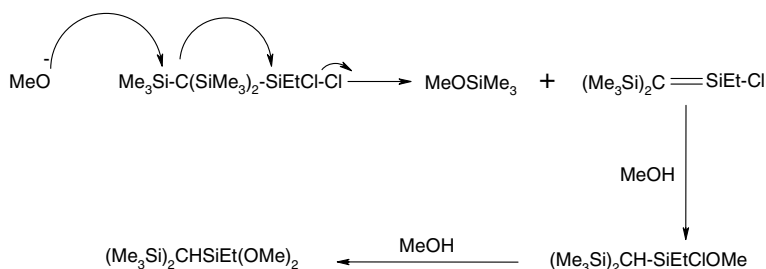
It has been shown previously that TsiLi reacts with MeSiCl₃, BuSiCl₃ and PhSiCl₃ to give the crowded disilanes TsiSiMeCl₂, TsiSiBuCl₂ and TsiSiPhCl₂, respectively, and we have now extended this reaction to the preparation of related TsiSiEtCl₂ and the study some of its reactions. The dichlorosilane, TsiSiEtCl₂, was prepared by the reaction of TsiLi with EtSiCl₃. Then direct replacement of the chloride by the small hydride ligand was effected by treatment with LiAlH₄, and direct nucleophilic substitution by reaction with pseudohalide salts such as NaN₃, NaOCN or KSCN in MeCN or MeOH (although the reactions in MeOH are accompanied by some formation of elimination–addition products) (Scheme 2). In the case of the reactions with KSCN, when the reaction was carried out for 48 h under reflux, the isolated product was exclusively the thiocyanate, TsiSiEt(SCN)₂, as indicated by the appearance of a bond at 2200 cm⁻¹ in the IR spectrum. When the reaction was followed by IR, the spectrum showed that with a reaction time of 3 days both isomers were present in the mixture with the appearance of bonds at 2200 and 2073 cm⁻¹ corresponding to SCN, NCS groups, respectively. Then the reaction was carried out 5 days under reflux, the isolated product was exclusively the thermodynamically more stable NCS derivative, TsiSiEt(NCS)₂. The reactions of TsiSiEtCl₂ with alkali metal salts in MeCN appear to be S_N2 nucleophilic displacements involving a five-coordinate intermediate; similar behavior was observed by Eaborn et al. [12,13] in the case of TsiSiMe₂X. The compound TsiSiEtCl₂ is cleaved by NaOMe/MeOH to give (Me₃Si)₂CHSiEt(OMe)₂. We postulate this reaction proceeds initially by the reaction of TsiSiEtCl₂ with NaOMe/MeOH to give (Me₃Si)₂CHSiEtClOMe. This type of reaction was also observed for all of the compounds TsiSiMe₂X with X = Cl, Br and TsiSiPh₂X with X = F, Cl, Br and I [2,14]. Direct nucleophilic displacement of chloride by methoxide gives (Me₃Si)₂CHSiEt(OMe)₂ (Scheme 1).

The initial process is analogous to an E₂ elimination from organic halides but with attack at a β-silicon rather than a β-hydrogen. That the nucleophile attacks at Me₃Si rather than at the electronically favored EtCl₂Si center can be attributed to the fact that attack at the former results in relief of more steric strain [2]. We also observed that treatment of TsiSiEtH₂ with a molar

proportion of ICl in CCl₄ gave the iodide TsiSiEtHI, which was converted into the di-iodide by a further molar proportion of ICl. Similar behavior was observed in the case of TsiSiMeH₂ [15]. However, it was shown previously that when TsiSiPhHI is treated with a one molar proportion of ICl the product is a 35:65 mixture of TsiSiPhClI and TsiSiPhI₂ [16]. The mode halogenation of TsiSiEtHI can be attributed to the presence of the sterically-undemanding hydrogen substituent in the transition state. The reaction essentially involves interaction of the electrophile with the electrons of the Si–H bond, and so attack by the positive end of the I–Cl dipole, as in. This concept was developed by Sommer for reactions with BrCl in terms of rate-determining formation of an intermediate ionic intermediate as in II, [16] which then rapidly breaks down by separation of HCl. The compound TsiSiEtIOMe was prepared from the reaction of the compound TsiSiEtHOME with ICl/CCl₄.



The hydride TsiSiEtH₂ has been reacted with two equivalent of Br₂ in CCl₄ to give the corresponding dibromide. The reaction of TsiSiEtH₂ with Br₂ or ICl (uncatalyzed by light) in CCl₄ is fast, and occurs with retention [17]. For the compounds of the type TsiSiR₂X with R = Me or Ph, X = F, Cl, Br, I, there is no reaction with methanol alone, but with sodium methoxide in methanol fragmentation occurs (presumably driven by release of steric strain) to give products of the type (Me₃Si)₂CHSiR₂OMe, seemingly via the silaolefins (Me₃Si)₂C = SiR₂ [11]. Replacement of one of the groups R by hydrogen reduce the steric hindrance considerably and our results for TsiSiEtHI show that nucleophilic substitution takes place readily. Mechanisms involving initial formation of a five-coordinate silicon complex have commonly been assumed in discussion of displacements at silicon atom in organosilicon compounds. Steric hindrance by the trisilyl group would be expected to prevent backside approach and force displacement from the same side as the leaving group and the observed substitution at silicon in TsiSiEtHI by MeOH and H₂O may



Scheme 1.

involve flank attack. The iodide TsiSiEtHI reacted with H₂O in dioxan in the presence of AgClO₄, and with dry MeOH to produce TsiSiEtHOH and TsiSiEtHOME respectively by direct bimolecular displacement reactions. Finally, the compound TsiSiEtI₂ reacted with H₂O in DMSO/MeCN to give TsiSiEt(OH)₂ during 24 h under reflux in 6/3/1 (vol./vol.) Me₂SO/MeCN/H₂O (the MeCN being added to increase the solubility of the iodide). This observation was of considerable significance, not only because it made the hydroxide available but also, more importantly, because the absence of rearranged product showed that the solvolysis did not proceed through a cationic intermediate [2]. It seems likely that formation of a five-coordinated intermediate is rate-determining (Scheme 2).

The 400 MHz NMR spectra of most of our compounds gave non-first-order ethyl resonances, as found previously for compounds TsiSiEt₂X and TsiSiEtMeX [16,17], but in those for TsiSiEtX₂ (X = I, OH, SCN, N₃) and TsiSiEtIOME the CH₃ and CH₂ resonances were clearly resolved.

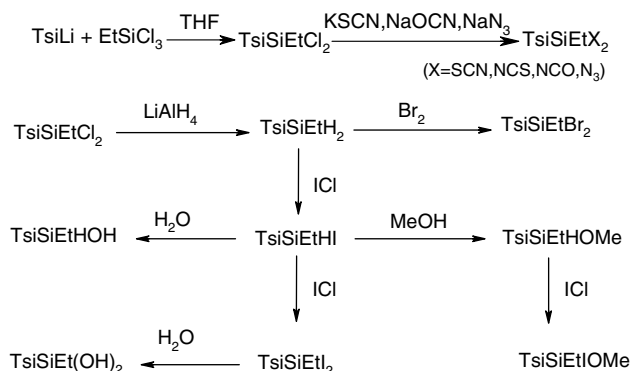
3. Experimental

3.1. Solvents and reagents

The reactions involving lithium metal, organolithium reagents, LiAlH₄, or alkoxides were carried out under dry argon. Solvents were dried by standard methods.

3.2. Spectra

Melting points were taken on an Electromental 9100-digital melting point apparatus. The ¹H NMR and ¹³C NMR spectra were recorded with a NMR Bruker. FT-400 MHz spectrometer at room temperature using CDCl₃ as a solvent. The mass spectra were obtained with a Finnigan–Mat model 8400, operating at 70 eV. The IR spectra were recorded on an FTIR, DR.8001–Shimadzu spectrometer. Elemental analyses were carried out with a Heareus CHN-ORAPID instrument.



Scheme 2.

3.3. Preparation of TsiSiEtCl₂

EtSiCl₃ (8.17 g, 50 mmol) was added dropwise with stirring to a solution of TsiLi (50 mmol) in THF (50 mL) that had been made by reaction of TsiH (11.5 g, 50 mmol) with MeLi (0.84 g, 120 mmol) (Prepared as described by Eaborn and his co-workers [18]). The mixture was refluxed for 30 min, then aqueous NH₄Cl was added and the organic layer was extracted with Et₂O. The extract was dried (MgSO₄), filtered, evaporated and the residue recrystallised from EtOH. A very pure product for elemental analysis was obtained by preparative TLC (silica gel, hexane as eluant) to give TsiSiEtCl₂ (62%), m.p. 308 °C. FTIR (KBr, cm⁻¹), (C–H aliphatic) 2960, (C–Si) 1250, 850, (Si–Cl) 675. ¹H NMR (CDCl₃) 0.34 (s, 27H, Tsi) and 1–1.25 ppm (m, 5H, Et). ¹³C NMR (CDCl₃) 1.7 (C–SiMe₃), 3.8 (CH₃Si), 6.0 (CH₃), 16.2 ppm (CH₂). *m/z* (EI): 344 (100%, [M – Me]⁺), 330 (5%, [M – Et]⁺), 140 (5%), 128 (20%), 73 (20%). (Found: C, 39.8; H, 8.8. C₁₁H₃₂Cl₂Si₄ Calc.: C, 40.1; H, 8.9%).

3.4. Preparation of TsiSiEt(SCN)₂

A mixture of TsiSiEtCl₂ (0.5 g, 1.4 mmol), KSCN (1.4 g, 14 mmol) and CH₃CN (100 mL) was refluxed for 48 h. The mixture was treated with water and Et₂O, the organic layer was separated, dried (MgSO₄), and filtered. Solvent was evaporated from the filtrate and the residue was purified by TLC (silica gel, *n*-hexane as eluent), (72%). m.p. 286 °C. FTIR (KBr, cm⁻¹), (SCN) 2200. ¹H NMR (CDCl₃) 0.24 (s, 27H, Tsi), 0.99–1.05 (q, 2H, CH₂), 1.14–1.18 ppm (t, 3H, CH₃). ¹³C NMR (CDCl₃) 0.8 (C–SiMe₃), 3.2 (CH₃–Si), 6.0 (CH₃), 11.8 ppm (CH₂). *m/z* (EI): 390 (30% [M – Me]⁺), 73 (100%, [Me₃Si]⁺), 259 (10%), 204 (5%), 130 (10%). (Found: C, 41.2; H, 7.8; N, 6.7. C₁₄H₃₂S₂N₂Si₄ Calc.: C, 41.5; H, 7.9; N, 6.9%).

3.5. Preparation of TsiSiEt(NCS)₂

A mixture of TsiSiEtCl₂ (0.5 g, 1.4 mmol) KSCN (1.4 g, 14 mmol) and MeCN (100 mL) was refluxed for 5 days. The mixture was treated with water and Et₂O. The organic layer was separated, dried (MgSO₄) and filtered. Solvent was evaporated from the filtrate and the residue was purified by TLC (Silica gel, *n*-hexane as eluent), (65%). m.p. 290 °C. FTIR (KBr, cm⁻¹), (NCS) 2073. ¹H NMR (CDCl₃) 0.28 (s, 27H, Tsi), 1.12–1.26 ppm (m, 5H, Et). ¹³C NMR (CDCl₃) 1.8 (C–SiMe₃), 3.3 (CH₃–Si), 5.9 (CH₃), 11.5 ppm (CH₂). *m/z* (EI): 390 (20% [M – Me]⁺), 259 (15%), 204 (10%), 73 (100%, [Me₃Si]⁺). (Found: C, 41.4; H, 7.8; N, 6.8 C₁₄H₃₂S₂N₂Si₄ Calc.: C, 41.5; H, 7.9; N, 6.9%).

3.6. Preparation of $TsSiEt(NCO)_2$

A mixture of $TsSiEtCl_2$ (0.5 g, 1.4 mmol), $NaOCN$ (0.9 g, 14 mmol) in MeCN (100 mL) was refluxed for 10 days. The mixture was treated with Et_2O and water, separated the organic layer was separated, dried ($MgSO_4$) and filtered. Solvent was evaporated from the filtrate and residue was purified by TLC (Silica gel, *n*-hexane as eluent), (53%). m.p. 303 °C. FTIR (KBr, cm^{-1}), (NCO) 2271. 1H NMR ($CDCl_3$) 0.34 (s, 27H, Tsi), 1.12–1.21 ppm (m, 5H, Et). ^{13}C NMR ($CDCl_3$), 2.2 (C–SiMe₃), 3.8 (Tsi), 8.5 (CH₃), 12.8 ppm (CH₂). *m/z* (EI): 372 (5% [M – Me]⁺), 359 (10%), 243 (5%), 73 (100%, [Me₃Si]⁺). (Found: C, 45.2; H, 8.5; N, 7.6. C₁₄H₃₂O₂N₂Si₄ Calc.: C, 45.1; H, 8.6; N, 7.5%).

3.7. Preparation of $TsSiEt(N_3)_2$

A mixture of $TsSiEtCl_2$ (0.5 g, 1.4 mmol) and NaN_3 (0.9 g, 14 mmol) in MeCN (100 mL) was refluxed for 3 days. The mixture was treated with water and Et_2O , the organic layer was separated, dried ($MgSO_4$) and filtered. Solvent was evaporated from the filtrate and residue was purified by TLC (Silica gel, *n*-hexane as eluent), (82%). m.p. 312 °C. FTIR (KBr, cm^{-1}), (N₃) 2100. 1H NMR ($CDCl_3$) 0.28 (s, 27H, Tsi), 0.99–1.05 (q, 2H, CH₂), 1.14–1.18 ppm (t, 3H, CH₃). ^{13}C NMR ($CDCl_3$), 2.8 (C–SiMe₃), 4.4 (Tsi), 7.0 (CH₃), 12.5 ppm (CH₂). *m/z* (EI): 358 (10%, [M – Me]⁺), 246 (10%), 131 (25%), 73 (100%, [Me₃Si]⁺). (Found: C, 38.5; H, 8.7; N, 22.7. C₁₂H₃₂N₆Si₄ Calc.: C, 38.6; H, 8.6 N, 22.5%).

3.8. Preparation of $(Me_3Si)_2CHSiEt(OMe)_2$

$TsSiEtCl_2$ (1 g, 2.8 mmol) was refluxed in 2 M $NaOCH_3/CH_3OH$ solution (30 mL) for 24 h. The solution was added to petroleum ether, the organic layer was washed several times with water, the organic layer was separated, dried ($MgSO_4$) and filtered. Solvent was evaporated from the filtrate and the residue was purified by TLC (silica gel, 90:10 *n*-hexane:dichloromethane as eluent) to give $(Me_3Si)_2CHSiEt(OMe)_2$. 1H NMR ($CDCl_3$): 0.1(s, 18H, Me₃Si), –0.6 (s, 1H, C–H), 0.5–1.5 (m, 5H, Et), 3.5 ppm (s, 1H, OMe). ^{13}C NMR ($CDCl_3$), 0.0 (C–H), 1.7(Me₃Si), 5.1 (CH₃), 12.6 (CH₂), 49.2 ppm (OMe). *m/z* (EI): 278 (30%, [M]⁺), 263 (80%, [M – Me]⁺), 182 (100%), 107 (20%), 77 (5%). (Found: C, 47.1; H, 10.5. C₁₁H₃₀Si₃O₂, Calc.: C, 47.5; H, 10.8%).

3.9. Preparation of $TsSiEtH_2$

$LiAlH_4$ (6 g, 0.158 mol) was gradually added with stirring to a solution of $TsSiEtCl_2$ (6 g, 16.7 mmol) in dried THF (150 mL). The mixture was refluxed for 2 days. After cooling of the mixture in ice water, aque-

ous saturated NH_4Cl was slowly added, the solution was extracted with Et_2O , then the extract was dried ($MgSO_4$) and filtered. Solvent was evaporated from the filtrate and the residue was recrystallized from $EtOH$ to give $TsSiEtH_2$ (82.5%). m.p. 210 °C. FTIR (KBr, cm^{-1}), (C–H) 2904, (Si–H) 2112, (C–Si) 1254, 850. 1H NMR ($CDCl_3$): 0.18 (s, 27H, Tsi), 0.76–1.04 (m, 5H, Et), 3.76–3.78 ppm (m, 2H, SiH₂). ^{13}C NMR ($CDCl_3$) 2.1 (C–SiMe₃), 2.3 (CH₃–Si), 2.5 (CH₃), 8.8 ppm(CH₂). *m/z* (EI): 289 (30%, [M – H]⁺), 275(100%, [M – Me]⁺), 273(80%), 242(40%), 201(50%). (Found: C, 49.8, H, 11.6. C₁₂H₃₄Si₄ Calc.: C, 49.6; H, 11.7%).

3.10. Preparation of $TsSiEtBr_2$

A solution of Br_2 (0.55 g, 3.34 mmol) in CCl_4 (25 ml) was added dropwise during a period of 30 min with stirring to a solution of $TsSiEtH_2$ (0.5 g, 1.72 mmol) in CCl_4 (10 mL) cooled in an ice bath. Then the mixture was stirred for an additional 30 min. at room temperature. Solvent was removed under reduced pressure (20 Torr) to leave a white residue, which was sublimed under reduced pressure (5 Torr) to give $TsSiEtBr_2$ (85%). m.p. 162 °C. 1H NMR ($CDCl_3$) 0.37 (27H, Tsi), 1.12–1.17 (t, 3H, CH₃) 1.20–1.37 ppm (m, 2H, CH₂). ^{13}C NMR ($CDCl_3$) 4.0 (C–SiMe₃), 4.1 (CH₃–Si), 6.7 (CH₃) 18.4 ppm (CH₂). *m/z* (EI): 433 (15%[M – Me]⁺), 389 (100%, [M – Et – 2Me]⁺), 343 (20%), 288 (70%.[M – 2Br]⁺), 221 (40%). (Found: C, 32.5, H, 7.6. C₁₁ H₃₂ Br₂ Si₄ Calc.: C, 32.1; H, 7.2%).

3.11. Preparation of $TsSiEtHI$

A solution of ICl (1.12 g, 6.9 mmol) in CCl_4 (30 mL) was added dropwise with stirring to a solution of $TsSiEtH_2$ (2 g, 6.89 mmol) in CCl_4 (20 mL). The mixture was stirred for 30 min and the solvent removed under reduced pressure (20 Torr) to leave a white residue, which was sublimed under reduced pressure (5 Torr) to give $TsSiEtHI$ (92%). m.p. 267 °C. FTIR (KBr, cm^{-1}), (Si–H) 2133. 1H NMR ($CDCl_3$) 0.32 (s, 27H, Tsi), 1.05–1.09 (t, 3H, CH₃) 1.10–1.23 (m, 2H, CH₂), 4.60–4.61 ppm (d, 1H, Si–H). ^{13}C NMR ($CDCl_3$) 2.2 (C–SiMe₃), 3.3 (CH₃–Si), 8.3 (CH₃), 12.5 ppm (CH₂). *m/z* (EI): 416 (5%, [M]⁺), 401 (90%, [M – Me]⁺), 313 (20%), 290 (100% [M – I]⁺), 72 (30%). (Found: C, 35; H, 8.1. C₁₁H₃₃ISi₄ Calc.: C, 34.6; H, 7.9%).

3.12. Preparation of $TsSiEtHOH$

A mixture of $AgClO_4$ (0.1 g), $TsSiEtHI$ (0.5 g, 1.2 mmol) dioxane (30 mL) and H_2O (5 mL) was refluxed for 2 h. The flask was covered with aluminum foil to avoid light. The mixture was cooled and filtered and

water (10 mL) was added. The organic material was extracted with *n*-hexane. The extract was dried (Na_2SO_4) and filtered. Solvent was evaporated from the filtrate and the residue was purified by TLC (Silica gel, 1:1 *n*-hexane: dichloromethane as eluent), (54%). m.p. 150 °C. FTIR (KBr, cm^{-1}), (OH) 3446, (Si–H) 2133. ^1H NMR (CDCl_3) 0.22 (s, 27H, Tsi), 0.74–0.85 (m, 2H, CH_2) 1.05–1.59 (t, 3H, CH_3), 1.54 (s, 1H, O–H), 4.68–4.69 ppm (d, 1H, Si–H). ^{13}C NMR (CDCl_3) 2.6 (C–SiMe₃), 3.5 (Tsi), 5.4 (CH_3), 10.2 ppm (CH_2). *m/z* (EI): 306 (5%, $[\text{M}]^+$), 291 (80%, $[\text{M} - \text{Me}]^+$), 289 (100%, $[\text{M} - \text{OH}]^+$), 275 (40%), 173 (10%), 72 (10%). (Found: C, 47.3; H; 10.8. $\text{C}_{11}\text{H}_{34}\text{OSi}_4$ Calc.: C, 47.1; H, 11.5%).

3.13. Preparation of TsiSiEtHOME

A mixture of TsiSiEtHI (0.5 g, 1.2 mmol) and methanol (40 mL) was refluxed for 48 h. The solvent was removed and the solid product was recrystallized from MeOH to yield TsiSiEtHOME (89%). m.p. 235 °C. FTIR (KBr, cm^{-1}), (Si–H) 2089, (Si–O) 1095. ^1H NMR (CDCl_3) 0.19 (s, 27 H, Tsi), 0.73–0.89 (m, 2H, CH_2) 1.08–1.12 (t, 3H, CH_3), 3.51 (s, 3H, OCH_3), 4.54–4.55 ppm (d, 1H, Si–H). ^{13}C NMR (CDCl_3) 2.8 (C–SiMe₃), 3.1 (Tsi), 8.2 (CH_3) 9.6 (CH_2), 52.2 ppm (OMe). *m/z* (EI): 305 (100% $[\text{M} - \text{Me}]^+$), 289 (20% $[\text{M} - \text{Me}]^+$), 201 (20%), 72 (10%). (Found: C, 48.8; H; 10.9. $\text{C}_{12}\text{H}_{36}\text{OSi}_4$ Calc.: C, 48.7; H, 11.2%).]

3.14. Preparation of TsiSiEtI(OMe)

A solution of ICl (0.15 g, 0.94 mmol) in CCl_4 (15 mL) was added dropwise with stirring to a solution of TsiSiEtH(OMe) (0.3 g, 0.94 mmol) in CCl_4 (15 mL). The mixture was stirred for 30 min and the solvent removed under reduced pressure (20 Torr) and leave a white residue. A pure product was obtained by preparative TLC (silica gel, *n*-hexane as eluant), (71%) m.p. 319 °C. ^1H NMR (CDCl_3), 0.32 (s, 27H, Tsi), 1.06–1.14 (t, 3H, Me) 1.38–1.42 (q, 2H, CH_2), 3.51 ppm (s, 3H, OMe). ^{13}C NMR (CDCl_3) 5.7 (C–SiMe₃), 6.0 (CH_3 –Si), 10.2 (CH_3), 20.5 (CH_2), 54.7 ppm (OMe). *m/z* (EI): 431 (20%, $[\text{M} - \text{Me}]^+$), 320 (100%, $[\text{M} - \text{I}]^+$), 319 (20%), 290 (10%, $[\text{M} - \text{I} - \text{Et}]^+$), 129 (10%), 72 (20%). (Found: C, 35.2; H; 7.8. $\text{C}_{12}\text{H}_{35}\text{IOSi}_4$, Calc.: C, 34.9; H, 7.8%).

3.15. Preparation of TsiSiEtI₂

A solution of ICl (0.56 g, 3.45 mmol) in CCl_4 (25 mL) was added dropwise with stirring to a solution of TsiSiEtH₂ (0.5 g, 1.72 mmol) in CCl_4 (10 mL). The mixture was stirred for 30 min and the solvent removed under reduced pressure (20 Torr). A very pure product for

elemental analysis was obtained by preparative TLC (silica gel, *n*-hexane as eluent), (94%). m.p. 280 °C. ^1H NMR (CDCl_3) 0.44 (s, 27H, Tsi) 1.08–1.12 (t, 3H, CH_3), 1.56–1.61 ppm (q, 2H, CH_2). ^{13}C NMR (CDCl_3) 4.3(C–Me₃), 4.9 (CH_3 –Si), 9.9 (CH_3) 18.4 ppm (CH_2). *m/z* (EI): 542(2%, $[\text{M}]^+$), 541(10%, $[\text{M} - \text{H}]^+$), 527(100%, $[\text{M} - \text{Me}]^+$), 513 (20%), 440 (60%), 416 (95%), (Found: C, 26.7; H, 6.2. $\text{C}_{11}\text{H}_{32}\text{I}_2\text{Si}_4$ Calc.: C, 26.5; H, 5.5%).

3.16. Preparation of TsiSiEt(OH)₂

A mixture of TsiSiEtI₂ (0.5 g, 0.93 mmol), DMSO (30 mL), H₂O (5 mL) and MeCN (15 mL) was refluxed for 24 h. The solution was treated with water (50 mL) and *n*-hexane (50 mL), dried (Na_2SO_4) and evaporated. A pure product was obtained by preparative TLC (Silica gel, dichloromethane as eluent), (64%). m.p. 255 °C. FTIR (KBr, cm^{-1}) (O–H) 3465. ^1H NMR (CDCl_3) 0.25 (s, 27H, Tsi), 0.73–0.79 (q, 2H, CH_2) 0.99–1.02 (t, 3H, CH_3), 1.97 ppm (s, 2H, OH). ^{13}C NMR (CDCl_3) 2.9 (C–SiMe₃), 3.5 (Tsi), 5.8 (CH_3), 10.5 ppm (CH_2). *m/z* (EI): 307 (10%, $[\text{M} - \text{Me}]^+$), 290 (100%, $[\text{M} - \text{Me} - \text{OH}]^+$) 276 (10%, $[\text{M} - \text{Et} - \text{OH}]^+$), 187 (10%), 72 (30%). (Found: C, 46.6, H, 10.5. $\text{C}_{11}\text{H}_{34}\text{O}_2\text{Si}_4$ Calc.: C, 44.70; H, 10.5%).

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